

Title (en)

DOPING MEDIA FOR THE LOCAL DOPING OF SILICON WAFERS

Title (de)

DOTIERMEDIEN ZUR LOKALEN DOTIERUNG VON SILIZIUMWAFERN

Title (fr)

SUBSTANCES DE DOPAGE DESTINÉES AU DOPAGE LOCAL DE TRANCHES DE SILICIUM

Publication

**EP 2938761 A1 20151104 (DE)**

Application

**EP 13817883 A 20131218**

Priority

- EP 12008660 A 20121228
- EP 13005734 A 20131210
- EP 13005735 A 20131210
- EP 13005736 A 20131210
- EP 13005737 A 20131210
- EP 2013003838 W 20131218
- EP 13817883 A 20131218

Abstract (en)

[origin: WO2014101989A1] The invention relates to a novel method for producing printable, high-viscous oxide media and to the use thereof in the production of solar cells.

IPC 8 full level

**C30B 31/04** (2006.01); **C09D 183/00** (2006.01); **C23C 18/12** (2006.01); **C23C 18/32** (2006.01); **H01L 21/02** (2006.01); **H01L 21/22** (2006.01); **H01L 21/225** (2006.01); **H01L 21/48** (2006.01); **H01L 31/0216** (2014.01); **H01L 31/0288** (2006.01)

CPC (source: EP US)

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Citation (search report)

See references of WO 2014101989A1

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BA ME

DOCDB simple family (publication)

**WO 2014101989 A1 20140703**; CN 104884685 A 20150902; EP 2938761 A1 20151104; JP 2016506630 A 20160303; JP 6383363 B2 20180829; KR 20150103131 A 20150909; SG 10201704400Y A 20170728; SG 11201504937V A 20150730; TW 201439373 A 20141016; TW I607115 B 20171201; US 10134942 B2 20181120; US 2015340541 A1 20151126

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**EP 2013003838 W 20131218**; CN 201380067938 A 20131218; EP 13817883 A 20131218; JP 2015550008 A 20131218; KR 20157020281 A 20131218; SG 10201704400Y A 20131218; SG 11201504937V A 20131218; TW 102148896 A 20131227; US 201314655857 A 20131218